



Integrated Device Technology, Inc.

HIGH-SPEED CMOS OCTAL D FLIP-FLOP WITH CLOCK ENABLE

IDT 54AHCT377

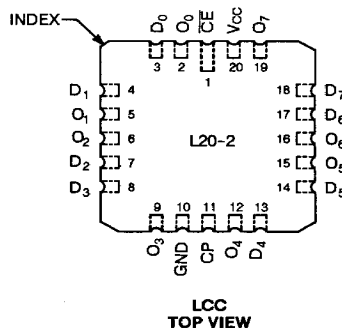
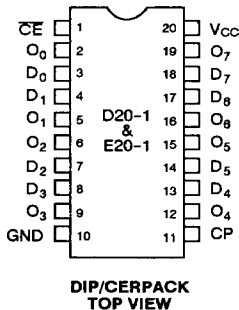
FEATURES:

- Equivalent to ALS speeds and output drive over full temperature and voltage supply extremes
- 10ns typical propagation delay
- $I_{OL} = 14mA$ over full military temperature range
- CMOS power levels (5 μ W typ. static)
- Both CMOS and TTL output compatible
- Substantially lower input current levels than ALS (5 μ A max.)
- Octal D flip-flop with clock enable
- JEDEC standard pinout for DIP and LCC
- Military product compliant to MIL-STD-883, Class B

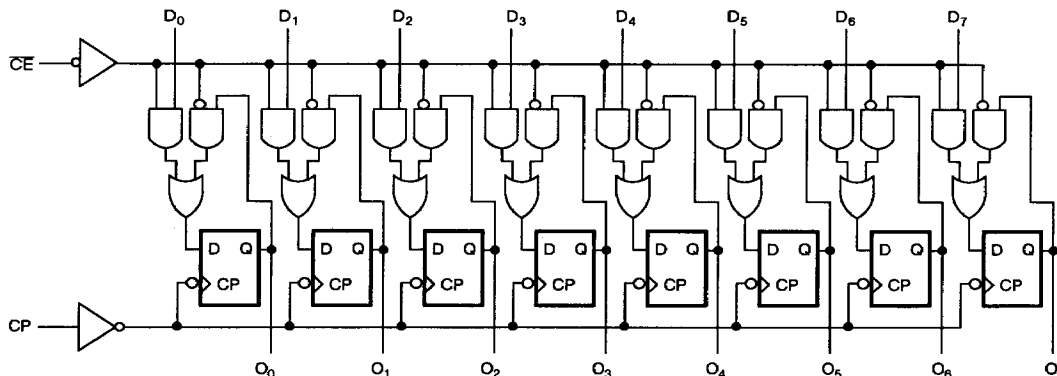
DESCRIPTION:

The IDT54AHCT377 is an octal D flip-flop built using advanced CEMOS™, a dual metal CMOS technology. The IDT54AHCT377 has eight edge-triggered, D-type flip-flops with individual D inputs and O outputs. The common buffered Clock (CP) input loads all flip-flops simultaneously when the Clock Enable (CE) is LOW. The register is fully edge-triggered. The state of each D input, one set-up time before the LOW-to-HIGH clock transition, is transferred to the corresponding flip-flop's O output. The CE input must be stable only one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

PIN CONFIGURATIONS



FUNCTIONAL BLOCK DIAGRAM



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MILITARY TEMPERATURE RANGE

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S10-184

DSC-4051/-1

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

SYMBOL	RATING	VALUE	UNIT
V _{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
T _A	Operating Temperature	-55 to +125	°C
T _{BIAS}	Temperature Under Bias	-65 to +135	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _T	Power Dissipation	0.5	W
I _{OUT}	DC Output Current	±20	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

SYMBOL	PARAMETER ⁽¹⁾	CONDITIONS	TYP.	MAX.	UNIT
C _{IN}	Input Capacitance	V _{IN} = 0V	6	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	8	12	pF

NOTE:

1. This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

T_A = -55°C to +125°C

V_{CC} = 5.0V ± 10%

V_{LC} = 0.2V

V_{HC} = V_{CC} - 0.2V

SYMBOL	PARAMETER	TEST CONDITIONS ⁽¹⁾	MIN.	TYP. ⁽²⁾	MAX.	UNIT
V _{IH}	Input HIGH Level	Guaranteed Logic High Level	2.0	—	—	V
V _{IL}	Input LOW Level	Guaranteed Logic Low Level	—	—	0.8	V
I _{IH}	Input HIGH Current	V _{CC} = Max., V _{IN} = V _{CC}	—	—	5.0	µA
I _{IL}	Input LOW Current	V _{CC} = Max., V _{IN} = GND	—	—	-5.0	µA
I _{SC}	Short Circuit Current	V _{CC} = Max. ⁽³⁾	-60	-100	—	mA
V _{OH}	Output HIGH Voltage	V _{CC} = 3V, V _{IN} = V _{LC} or V _{HC} , I _{OH} = -32µA	V _{HC}	V _{CC}	—	mA
		V _{CC} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OH} = -150µA I _{OH} = -1.0mA	V _{HC}	V _{CC}	—
V _{OL}	Output LOW Voltage	V _{CC} = 3V, V _{IN} = V _{LC} or V _{HC} , I _{OL} = 300µA	—	GND	V _{LC}	—
		V _{CC} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OL} = 300µA I _{OL} = 14mA	—	GND	V _{LC}

NOTES:

- For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

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POWER SUPPLY CHARACTERISTICS

$V_{LC} = 0.2V; V_{HC} = V_{CC} - 0.2V$

SYMBOL	PARAMETER	TEST CONDITIONS ⁽¹⁾		MIN.	TYP. ⁽²⁾	MAX.	UNIT
I_{CCO}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$ $V_{IN} \geq V_{HC}; V_{IN} \leq V_{LC}$ $f_{CP} = f_I = 0$		—	0.001	1.5	mA
I_{CCT}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current ⁽⁵⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{CE} = \text{GND}$ One Bit Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$	—	0.15	0.25	mA/ MHz
I_{CC}	Total Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 10\text{MHz}$ 50% Duty Cycle $\overline{CE} = \text{GND}$ One Bit Toggling at $f_I = 500\text{kHz}$ 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (AHCT)	—	0.15	1.8	mA
			$V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$	—	0.65	3.8	
		$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 1.0\text{MHz}$ 50% Duty Cycle $\overline{CE} = \text{GND}$ Eight Bits Toggling at $f_I = 250\text{kHz}$ 50% Duty Cycle	$V_{IN} \geq V_{HC}^{(6)}$ $V_{IN} \leq V_{LC}$ (AHCT)	—	0.63	2.2	
			$V_{IN} = 3.4V$ or ⁽⁶⁾ $V_{IN} = \text{GND}$	—	2.88	11.2	

NOTES:

- For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 5.0V, +25^\circ\text{C}$ ambient and maximum loading.
- Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.
- $I_{CC} = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_{CC} = I_{CCO} + I_{CCT} D_H N_T + I_{CCD} (f_{CP}/2 + f_I N_I)$
 I_{CCO} = Quiescent Current
 I_{CCT} = Power Supply Current for a TTL High Input ($V_{IN} = 3.4V$)
 D_H = Duty Cycle for TTL Inputs High
 N_T = Number of TTL inputs at D_H
 I_{CCD} = Dynamic Current caused by an input Transition pair (HLH or LHL)
 f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)
 f_I = Input Frequency
 N_I = Number of inputs at f_I
 All currents are in milliamps and all frequencies are in megahertz.
- This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
- Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

DEFINITION OF FUNCTIONAL TERMS

PIN NAMES	DESCRIPTION
D ₀ -D ₇	Data Inputs
\overline{CE}	Clock Enable (Active LOW)
O ₀ -O ₇	Data Outputs
CP	Clock Pulse Input

TRUTH TABLE

OPERATING MODE	INPUTS			OUTPUTS
	CP	CE	D	O
Load "1"	↑	l	h	H
Load "0"	↑	l	l	L
Hold (Do Nothing)	↑ X	h H	X	No Change No Change

H = HIGH Voltage Level
h = HIGH Voltage Level one setup time prior to the LOW-to-HIGH Clock Transition
L = LOW Voltage Level
l = LOW Voltage Level one setup time prior to the LOW-to-HIGH Clock Transition
X = Immaterial
↑ = LOW-to-HIGH Clock Transition

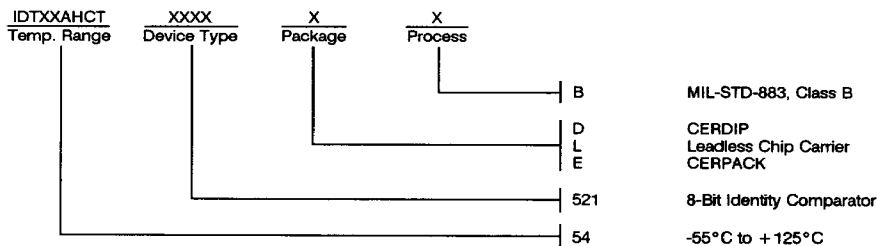
SWITCHING CHARACTERISTICS OVER OPERATING RANGE

SYMBOL	PARAMETER	CONDITION ⁽¹⁾	TYP.	MIN. ⁽²⁾	MAX.	UNIT
t _{PLH} t _{PHL}	Propagation Delay CP to O _N	C _L = 50pF R _L = 500Ω	10.0	2.0	20.0	ns
t _S	Set-up Time HIGH or LOW D _N to CP		5.0	2.0	—	ns
t _H	Hold Time HIGH or LOW D _N to CP		2.0	1.5	—	ns
t _S	Set-up Time HIGH or LOW CE to CP		3.0	4.0	—	ns
t _H	Hold Time HIGH or LOW CE to CP		2.0	1.5	—	ns
t _w	Clock Pulse Width, LOW		7.0	7.0	—	ns

NOTES:

- See test circuit and waveform.
- Minimum limits are guaranteed but not tested on Propagation Delays.

ORDERING INFORMATION



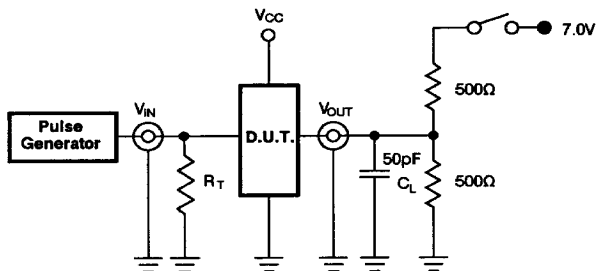
CMOS TESTING CONSIDERATIONS

Special test board considerations must be taken into account when applying high-speed CMOS products to the automatic test environment. Large output currents are being switched in very short periods and proper testing demands that test set-ups have minimized inductance and guaranteed zero voltage grounds. The techniques listed below will assist the user in obtaining accurate testing results:

1. All input pins should be connected to a voltage potential during testing. If left floating, the device may oscillate, causing improper device operation and possible latchup.
2. Placement and value of decoupling capacitors is critical. Each physical set-up has different electrical characteristics and it is recommended that various decoupling capacitor sizes be experimented with. Capacitors should be positioned using the minimum lead lengths. They should also be distributed to decouple power supply lines and be placed as close as possible to the DUT power pins.
3. Device grounding is extremely critical for proper device testing. The use of multi-layer performance boards with radial decoupling between power and ground planes is necessary. The ground plane must be sustained from the performance board to the DUT interface board and wiring unused interconnect pins to the ground plane is recommended. Heavy gauge stranded wire should be used for power wiring, with twisted pairs being recommended for minimized inductance.
4. To guarantee data sheet compliance, the input thresholds should be tested per input pin in a static environment. To allow for hardware-induced noise, it may be necessary to use $V_{IL} \leq 0V$ and $V_{IH} \geq 3V$ for ATE testing purposes.

TEST CIRCUITS AND WAVEFORMS

TEST CIRCUITS FOR THREE-STATE OUTPUTS



SWITCH POSITION

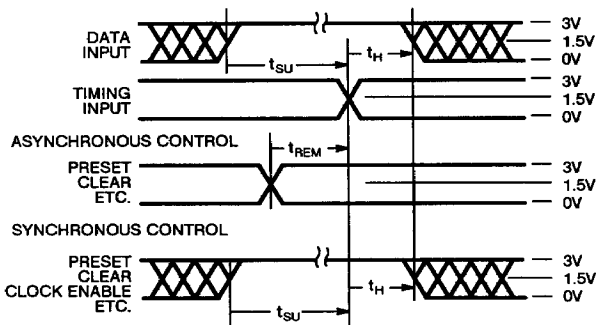
TEST	SWITCH
Open Drain Disable Low Enable Low	Closed
All Other Outputs	Open

DEFINITIONS

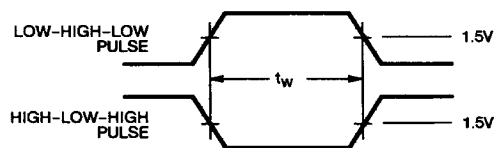
C_L = Load capacitance: includes jig and probe capacitance

R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator

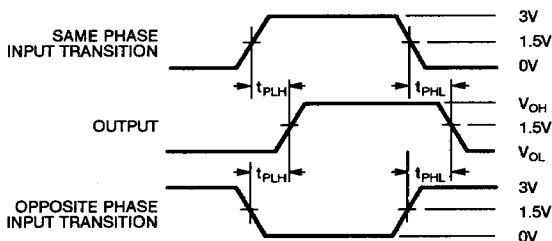
SET-UP, HOLD, AND RELEASE TIMES



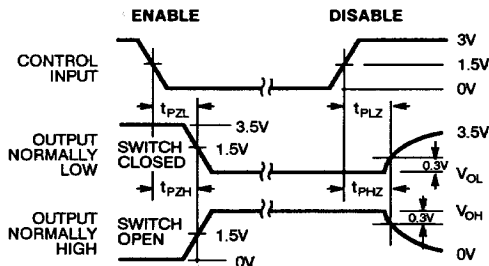
PULSE WIDTH



PROPAGATION DELAY



ENABLE AND DISABLE TIMES



NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH
- Pulse Generator for All Pulses: Rate ≤ 1.0 MHz; $Z_O \leq 50\Omega$; $t_F \leq 2.5$ ns; $t_R \leq 2.5$ ns

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